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研究成果目錄：論文及著述

A. 期刊論文

國外期刊

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- 55, No.12, pp. 3569~3574, December, 2008.
9. R. Y. Su, P. Y. Chiang, J. Gong, T. Y. Huang, C. L. Tsai, C. C. Chou and C.M. Liu, "Experimental results of On-state Resistance Reduction by STI Fingers in LDMOSFET", IEEE Electron Device Letters, Vol. 30, pp. 192-194, Feb., 2009.
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B. 研討會論文 國內研討會

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 6. Wan-Jyun Syue, Jeng Gong, Kai-Yuen Lam, “Resistance Extraction of High Voltage Lateral Diffused Metal-Oxide-Semiconductor Field-Effect Transistor”, Proceedings of the 28th Symposium on Electrical Power Engineering, pp. E08.5-1~E08.5-4, 2007.

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